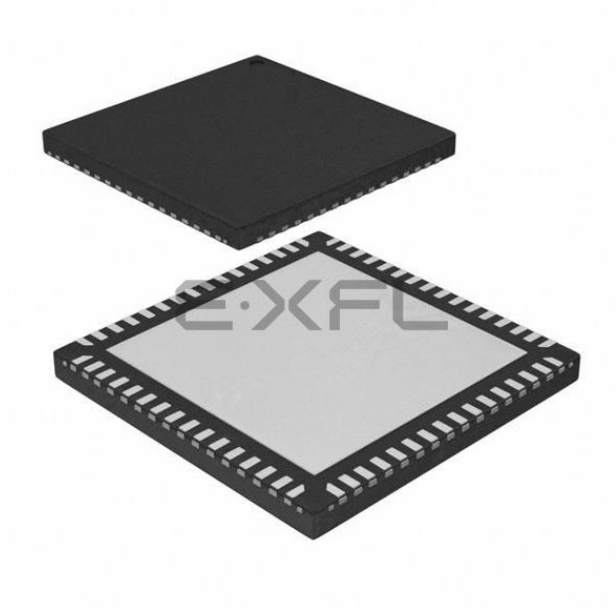

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Discontinued at Digi-Key
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	CANbus, I²C, IrDA, LINbus, SmartCard, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, I²S, LCD, POR, PWM, WDT
Number of I/O	56
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.8V
Data Converters	A/D 12bit SAR; D/A 12bit
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-VFQFN Exposed Pad
Supplier Device Package	64-QFN (9x9)
Purchase URL	https://www.e-xfl.com/product-detail/silicon-labs/efm32tg11b340f64gm64-ar

Ordering Code	Flash (kB)	RAM (kB)	DC-DC Con-verter	LCD	GPIO	Package	Temp Range
EFM32TG11B320F128GQ48-A	128	32	No	Yes	37	QFP48	-40 to +85°C
EFM32TG11B320F128IQ48-A	128	32	No	Yes	37	QFP48	-40 to +125°C
EFM32TG11B340F64GQ48-A	64	32	No	Yes	37	QFP48	-40 to +85°C
EFM32TG11B340F64IQ48-A	64	32	No	Yes	37	QFP48	-40 to +125°C
EFM32TG11B120F128GM64-A	128	32	No	No	56	QFN64	-40 to +85°C
EFM32TG11B120F128GQ64-A	128	32	No	No	53	QFP64	-40 to +85°C
EFM32TG11B120F128IM64-A	128	32	No	No	56	QFN64	-40 to +125°C
EFM32TG11B120F128IQ64-A	128	32	No	No	53	QFP64	-40 to +125°C
EFM32TG11B140F64GM64-A	64	32	No	No	56	QFN64	-40 to +85°C
EFM32TG11B140F64GQ64-A	64	32	No	No	53	QFP64	-40 to +85°C
EFM32TG11B140F64IM64-A	64	32	No	No	56	QFN64	-40 to +125°C
EFM32TG11B140F64IQ64-A	64	32	No	No	53	QFP64	-40 to +125°C
EFM32TG11B120F128GQ48-A	128	32	No	No	37	QFP48	-40 to +85°C
EFM32TG11B120F128IQ48-A	128	32	No	No	37	QFP48	-40 to +125°C
EFM32TG11B140F64GQ48-A	64	32	No	No	37	QFP48	-40 to +85°C
EFM32TG11B140F64IQ48-A	64	32	No	No	37	QFP48	-40 to +125°C
EFM32TG11B120F128GM32-A	128	32	No	No	24	QFN32	-40 to +85°C
EFM32TG11B120F128IM32-A	128	32	No	No	24	QFN32	-40 to +125°C
EFM32TG11B140F64GM32-A	64	32	No	No	24	QFN32	-40 to +85°C
EFM32TG11B140F64IM32-A	64	32	No	No	24	QFN32	-40 to +125°C

3.6.5 Controller Area Network (CAN)

The CAN peripheral provides support for communication at up to 1 Mbps over CAN protocol version 2.0 part A and B. It includes 32 message objects with independent identifier masks and retains message RAM in EM2. Automatic retransmittion may be disabled in order to support Time Triggered CAN applications.

3.6.6 Peripheral Reflex System (PRS)

The Peripheral Reflex System provides a communication network between different peripheral modules without software involvement. Peripheral modules producing Reflex signals are called producers. The PRS routes Reflex signals from producers to consumer peripherals which in turn perform actions in response. Edge triggers and other functionality such as simple logic operations (AND, OR, NOT) can be applied by the PRS to the signals. The PRS allows peripheral to act autonomously without waking the MCU core, saving power.

3.6.7 Low Energy Sensor Interface (LESENSE)

The Low Energy Sensor Interface LESENSE™ is a highly configurable sensor interface with support for up to 16 individually configurable sensors. By controlling the analog comparators, ADC, and DAC, LESENSE is capable of supporting a wide range of sensors and measurement schemes, and can for instance measure LC sensors, resistive sensors and capacitive sensors. LESENSE also includes a programmable finite state machine which enables simple processing of measurement results without CPU intervention. LESENSE is available in energy mode EM2, in addition to EM0 and EM1, making it ideal for sensor monitoring in applications with a strict energy budget.

3.7 Security Features

3.7.1 GPCRC (General Purpose Cyclic Redundancy Check)

The GPCRC module implements a Cyclic Redundancy Check (CRC) function. It supports both 32-bit and 16-bit polynomials. The supported 32-bit polynomial is 0x04C11DB7 (IEEE 802.3), while the 16-bit polynomial can be programmed to any value, depending on the needs of the application.

3.7.2 Crypto Accelerator (CRYPTO)

The Crypto Accelerator is a fast and energy-efficient autonomous hardware encryption and decryption accelerator. Tiny Gecko Series 1 devices support AES encryption and decryption with 128- or 256-bit keys, ECC over both GF(P) and GF(2^m), and SHA-1 and SHA-2 (SHA-224 and SHA-256).

Supported block cipher modes of operation for AES include: ECB, CTR, CBC, PCBC, CFB, OFB, GCM, CBC-MAC, GMAC and CCM.

Supported ECC NIST recommended curves include P-192, P-224, P-256, K-163, K-233, B-163 and B-233.

The CRYPTO module allows fast processing of GCM (AES), ECC and SHA with little CPU intervention. CRYPTO also provides trigger signals for DMA read and write operations.

3.7.3 True Random Number Generator (TRNG)

The TRNG module is a non-deterministic random number generator based on a full hardware solution. The TRNG is validated with NIST800-22 and AIS-31 test suites as well as being suitable for FIPS 140-2 certification (for the purposes of cryptographic key generation).

3.7.4 Security Management Unit (SMU)

The Security Management Unit (SMU) allows software to set up fine-grained security for peripheral access, which is not possible in the Memory Protection Unit (MPU). Peripherals may be secured by hardware on an individual basis, such that only priveleged accesses to the peripheral's register interface will be allowed. When an access fault occurs, the SMU reports the specific peripheral involved and can optionally generate an interrupt.

3.8 Analog

3.10 Core and Memory

3.10.1 Processor Core

The ARM Cortex-M processor includes a 32-bit RISC processor integrating the following features and tasks in the system:

- ARM Cortex-M0+ RISC processor
- Memory Protection Unit (MPU) supporting up to 8 memory segments
- Micro-Trace Buffer (MTB)
- Up to 128 kB flash program memory
- Up to 32 kB RAM data memory
- Configuration and event handling of all modules
- 2-pin Serial-Wire debug interface

3.10.2 Memory System Controller (MSC)

The Memory System Controller (MSC) is the program memory unit of the microcontroller. The flash memory is readable and writable from both the Cortex-M and DMA. The flash memory is divided into two blocks; the main block and the information block. Program code is normally written to the main block, whereas the information block is available for special user data and flash lock bits. There is also a read-only page in the information block containing system and device calibration data. Read and write operations are supported in energy modes EM0 Active and EM1 Sleep.

3.10.3 Linked Direct Memory Access Controller (LDMA)

The Linked Direct Memory Access (LDMA) controller allows the system to perform memory operations independently of software. This reduces both energy consumption and software workload. The LDMA allows operations to be linked together and staged, enabling sophisticated operations to be implemented.

3.10.4 Bootloader

All devices come pre-programmed with a UART bootloader. This bootloader resides in flash and can be erased if it is not needed. More information about the bootloader protocol and usage can be found in *AN0003: UART Bootloader*. Application notes can be found on the Silicon Labs website (www.silabs.com/32bit-appnotes) or within Simplicity Studio in the [**Documentation**] area.

4.1.2 Operating Conditions

When assigning supply sources, the following requirements must be observed:

- VREGVDD must be greater than or equal to AVDD, DVDD and all IOVDD supplies.
- VREGVDD = AVDD
- DVDD ≤ AVDD
- IOVDD ≤ AVDD

4.1.5 Backup Supply Domain

Table 4.5. Backup Supply Domain

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Backup supply voltage range	V_{BU_VIN}		TBD	—	3.8	V
PWRRES resistor	R_{PWRRES}	EMU_BUCTRL_PWRRES = RES0	TBD	3900	TBD	Ω
		EMU_BUCTRL_PWRRES = RES1	TBD	1800	TBD	Ω
		EMU_BUCTRL_PWRRES = RES2	TBD	1330	TBD	Ω
		EMU_BUCTRL_PWRRES = RES3	TBD	815	TBD	Ω
Output impedance between BU_VIN and BU_VOUT [2]	R_{BU_VOUT}	EMU_BUCTRL_VOUTRES = STRONG	TBD	110	TBD	Ω
		EMU_BUCTRL_VOUTRES = MED	TBD	775	TBD	Ω
		EMU_BUCTRL_VOUTRES = WEAK	TBD	6500	TBD	Ω
Supply current	I_{BU_VIN}	BU_VIN not powering backup domain	—	10	TBD	nA
		BU_VIN powering backup domain[1]	—	450	TBD	nA

Note:

1. Additional current required by backup circuitry when backup is active. Includes supply current of backup switches and backup regulator. Does not include supply current required for backed-up circuitry.
2. BU_VOUT and BU_STAT signals are not available in all package configurations. Check the device pinout for availability.

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Current consumption in EM4H mode, with voltage scaling enabled	I_{EM4H_VS}	128 byte RAM retention, RTCC running from LFXO	—	0.82	—	µA
		128 byte RAM retention, CRYOTIMER running from ULFRCO	—	0.45	—	µA
		128 byte RAM retention, no RTCC	—	0.45	TBD	µA
Current consumption in EM4S mode	I_{EM4S}	No RAM retention, no RTCC	—	0.07	TBD	µA
Current consumption of peripheral power domain 1, with voltage scaling enabled	I_{PD1_VS}	Additional current consumption in EM2/3 when any peripherals on power domain 1 are enabled[1]	—	0.18	—	µA
Current consumption of peripheral power domain 2, with voltage scaling enabled	I_{PD2_VS}	Additional current consumption in EM2/3 when any peripherals on power domain 2 are enabled[1]	—	0.18	—	µA

Note:

1. Extra current consumed by power domain. Does not include current associated with the enabled peripherals. See 3.2.3 EM2 and EM3 Power Domains for a list of the peripherals in each power domain.
2. CMU_LFRCOCTRL_ENVREF = 1, CMU_LFRCOCTRL_VREFUPDATE = 1

4.1.6.2 Current Consumption 3.3 V using DC-DC Converter

Unless otherwise indicated, typical conditions are: VREGVDD = AVDD = IOVDD = 3.3 V, DVDD = 1.8 V DC-DC output. T = 25 °C. Minimum and maximum values in this table represent the worst conditions across supply voltage and process variation at T = 25 °C.

Table 4.7. Current Consumption 3.3 V using DC-DC Converter

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Current consumption in EM0 mode with all peripherals disabled, DCDC in Low Noise DCM mode[2]	I_{ACTIVE_DCM}	48 MHz crystal, CPU running while loop from flash	—	38	—	µA/MHz
		48 MHz HFRCO, CPU running while loop from flash	—	37	—	µA/MHz
		48 MHz HFRCO, CPU running Prime from flash	—	45	—	µA/MHz
		48 MHz HFRCO, CPU running CoreMark loop from flash	—	53	—	µA/MHz
		32 MHz HFRCO, CPU running while loop from flash	—	43	—	µA/MHz
		26 MHz HFRCO, CPU running while loop from flash	—	47	—	µA/MHz
		16 MHz HFRCO, CPU running while loop from flash	—	61	—	µA/MHz
		1 MHz HFRCO, CPU running while loop from flash	—	587	—	µA/MHz
Current consumption in EM0 mode with all peripherals disabled, DCDC in Low Noise CCM mode[1]	I_{ACTIVE_CCM}	48 MHz crystal, CPU running while loop from flash	—	49	—	µA/MHz
		48 MHz HFRCO, CPU running while loop from flash	—	48	—	µA/MHz
		48 MHz HFRCO, CPU running Prime from flash	—	55	—	µA/MHz
		48 MHz HFRCO, CPU running CoreMark loop from flash	—	63	—	µA/MHz
		32 MHz HFRCO, CPU running while loop from flash	—	60	—	µA/MHz
		26 MHz HFRCO, CPU running while loop from flash	—	68	—	µA/MHz
		16 MHz HFRCO, CPU running while loop from flash	—	96	—	µA/MHz
		1 MHz HFRCO, CPU running while loop from flash	—	1157	—	µA/MHz
Current consumption in EM0 mode with all peripherals disabled, DCDC in LP mode[3]	I_{ACTIVE_LPM}	32 MHz HFRCO, CPU running while loop from flash	—	32	—	µA/MHz
		26 MHz HFRCO, CPU running while loop from flash	—	33	—	µA/MHz
		16 MHz HFRCO, CPU running while loop from flash	—	36	—	µA/MHz
		1 MHz HFRCO, CPU running while loop from flash	—	156	—	µA/MHz

4.1.9.5 Auxiliary High-Frequency RC Oscillator (AUXHFRCO)

Table 4.15. Auxiliary High-Frequency RC Oscillator (AUXHFRCO)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Frequency accuracy	$f_{AUXHFRCO\_ACC}$	At production calibrated frequencies, across supply voltage and temperature	TBD	—	TBD	%
Start-up time	$t_{AUXHFRCO}$	$f_{AUXHFRCO} \geq 19$ MHz	—	400	—	ns
		$4 < f_{AUXHFRCO} < 19$ MHz	—	1.4	—	µs
		$f_{AUXHFRCO} \leq 4$ MHz	—	2.5	—	µs
Current consumption on all supplies	$I_{AUXHFRCO}$	$f_{AUXHFRCO}$ = 48 MHz	—	238	TBD	µA
		$f_{AUXHFRCO}$ = 38 MHz	—	196	TBD	µA
		$f_{AUXHFRCO}$ = 32 MHz	—	160	TBD	µA
		$f_{AUXHFRCO}$ = 26 MHz	—	137	TBD	µA
		$f_{AUXHFRCO}$ = 19 MHz	—	110	TBD	µA
		$f_{AUXHFRCO}$ = 16 MHz	—	101	TBD	µA
		$f_{AUXHFRCO}$ = 13 MHz	—	78	TBD	µA
		$f_{AUXHFRCO}$ = 7 MHz	—	54	TBD	µA
		$f_{AUXHFRCO}$ = 4 MHz	—	30	TBD	µA
		$f_{AUXHFRCO}$ = 2 MHz	—	27	TBD	µA
		$f_{AUXHFRCO}$ = 1 MHz	—	25	TBD	µA
Coarse trim step size (% of period)	$SS_{AUXHFRCO\_COARSE}$		—	0.8	—	%
Fine trim step size (% of period)	$SS_{AUXHFRCO\_FINE}$		—	0.1	—	%
Period jitter	$PJ_{AUXHFRCO}$		—	0.2	—	% RMS

4.1.9.6 Ultra-low Frequency RC Oscillator (ULFRCO)

Table 4.16. Ultra-low Frequency RC Oscillator (ULFRCO)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Oscillation frequency	f_{ULFRCO}		TBD	1	TBD	kHz

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Hysteresis (V_{CM} = 1.25 V, BIASPROG[4] = 0x10, FULLBIAS[4] = 1)	$V_{ACMPHYST}$	HYSTSEL[5] = HYST0	TBD	0	TBD	mV
		HYSTSEL[5] = HYST1	TBD	18	TBD	mV
		HYSTSEL[5] = HYST2	TBD	33	TBD	mV
		HYSTSEL[5] = HYST3	TBD	46	TBD	mV
		HYSTSEL[5] = HYST4	TBD	57	TBD	mV
		HYSTSEL[5] = HYST5	TBD	68	TBD	mV
		HYSTSEL[5] = HYST6	TBD	79	TBD	mV
		HYSTSEL[5] = HYST7	TBD	90	TBD	mV
		HYSTSEL[5] = HYST8	TBD	0	TBD	mV
		HYSTSEL[5] = HYST9	TBD	-18	TBD	mV
		HYSTSEL[5] = HYST10	TBD	-33	TBD	mV
		HYSTSEL[5] = HYST11	TBD	-45	TBD	mV
		HYSTSEL[5] = HYST12	TBD	-57	TBD	mV
		HYSTSEL[5] = HYST13	TBD	-67	TBD	mV
		HYSTSEL[5] = HYST14	TBD	-78	TBD	mV
		HYSTSEL[5] = HYST15	TBD	-88	TBD	mV
Comparator delay[3]	$t_{ACMPDELAY}$	BIASPROG[4] = 1, FULLBIAS[4] = 0	—	30	—	µs
		BIASPROG[4] = 0x10, FULLBIAS[4] = 0	—	3.7	—	µs
		BIASPROG[4] = 0x02, FULLBIAS[4] = 1	—	360	—	ns
		BIASPROG[4] = 0x20, FULLBIAS[4] = 1	—	35	—	ns
Offset voltage	$V_{ACMPOFFSET}$	BIASPROG[4] =0x10, FULLBIAS[4] = 1	TBD	—	TBD	mV
Reference voltage	$V_{ACMPREF}$	Internal 1.25 V reference	TBD	1.25	TBD	V
		Internal 2.5 V reference	TBD	2.5	TBD	V
Capacitive sense internal resistance	R_{CSRES}	CSRESSEL[6] = 0	—	infinite	—	kΩ
		CSRESSEL[6] = 1	—	15	—	kΩ
		CSRESSEL[6] = 2	—	27	—	kΩ
		CSRESSEL[6] = 3	—	39	—	kΩ
		CSRESSEL[6] = 4	—	51	—	kΩ
		CSRESSEL[6] = 5	—	100	—	kΩ
		CSRESSEL[6] = 6	—	162	—	kΩ
		CSRESSEL[6] = 7	—	235	—	kΩ

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit

Note:

1. Specified configuration for 3X-Gain configuration is: INCBW = 1, HCMDIS = 1, RESINSEL = VSS, V_{INPUT} = 0.5 V, V_{OUTPUT} = 1.5 V. Nominal voltage gain is 3.
2. If the maximum C_{LOAD} is exceeded, an isolation resistor is required for stability. See AN0038 for more information.
3. When INCBW is set to 1 the OPAMP bandwidth is increased. This is allowed only when the non-inverting close-loop gain is ≥ 3, or the OPAMP may not be stable.
4. Current into the load resistor is excluded. When the OPAMP is connected with closed-loop gain > 1, there will be extra current to drive the resistor feedback network. The internal resistor feedback network has total resistance of 143.5 kOhm, which will cause another ~10 µA current when the OPAMP drives 1.5 V between output and ground.
5. Step between 0.2V and V_{OPA}-0.2V, 10%-90% rising/falling range.
6. From enable to output settled. In sample-and-off mode, RC network after OPAMP will contribute extra delay. Settling error < 1mV.
7. In unit gain connection, UGF is the gain-bandwidth product of the OPAMP. In 3x Gain connection, UGF is the gain-bandwidth product of the OPAMP and 1/3 attenuation of the feedback network.
8. Specified configuration for Unit gain buffer configuration is: INCBW = 0, HCMDIS = 0, RESINSEL = DISABLE. V_{INPUT} = 0.5 V, V_{OUTPUT} = 0.5 V.
9. When HCMDIS=1 and input common mode transitions the region from V_{OPA}-1.4V to V_{OPA}-1V, input offset will change. PSRR and CMRR specifications do not apply to this transition region.

4.1.18 LCD Driver

Table 4.25. LCD Driver

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Frame rate	f_{LCDFR}		TBD	—	TBD	Hz
LCD supply range[2]	V_{LCDIN}		1.8	—	3.8	V
LCD output voltage range	V_{LCD}	Current source mode, No external LCD capacitor	2.0	—	V_{LCDIN}-0.4	V
		Step-down mode with external LCD capacitor	2.0	—	V_{LCDIN}	V
		Charge pump mode with external LCD capacitor	2.0	—	Min of 3.8 and 1.9 * V_{LCDIN}	V
Contrast control step size	$STEP_{CONTRAST}$	Current source mode	—	64	—	mV
		Charge pump or Step-down mode	—	43	—	mV
Contrast control step accuracy[1]	$ACC_{CONTRAST}$		—	+/-4	—	%

Note:

1. Step size accuracy is measured relative to the typical step size, and typ value represents one standard deviation.
2. V_{LCDIN} is selectable between the AVDD or DVDD supply pins, depending on EMU_PWRCTRL_ANASW.

4.1.19 Pulse Counter (PCNT)

Table 4.26. Pulse Counter (PCNT)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Input frequency	F_{IN}	Asynchronous Single and Quadrature Modes	—	—	20	MHz
		Sampled Modes with Debounce filter set to 0.	—	—	8	kHz

4.1.20 Analog Port (APORT)

Table 4.27. Analog Port (APORT)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Supply current[2] [1]	I_{APORT}	Operation in EM0/EM1	—	7	—	µA
		Operation in EM2/EM3	—	915	—	nA

Note:

1. Specified current is for continuous APORT operation. In applications where the APORT is not requested continuously (e.g. periodic ACMP requests from LESENSE in EM2), the average current requirements can be estimated by mutiplying the duty cycle of the requests by the specified continuous current number.
2. Supply current increase that occurs when an analog peripheral requests access to APORT. This current is not included in reported module currents. Additional peripherals requesting access to APORT do not incur further current.

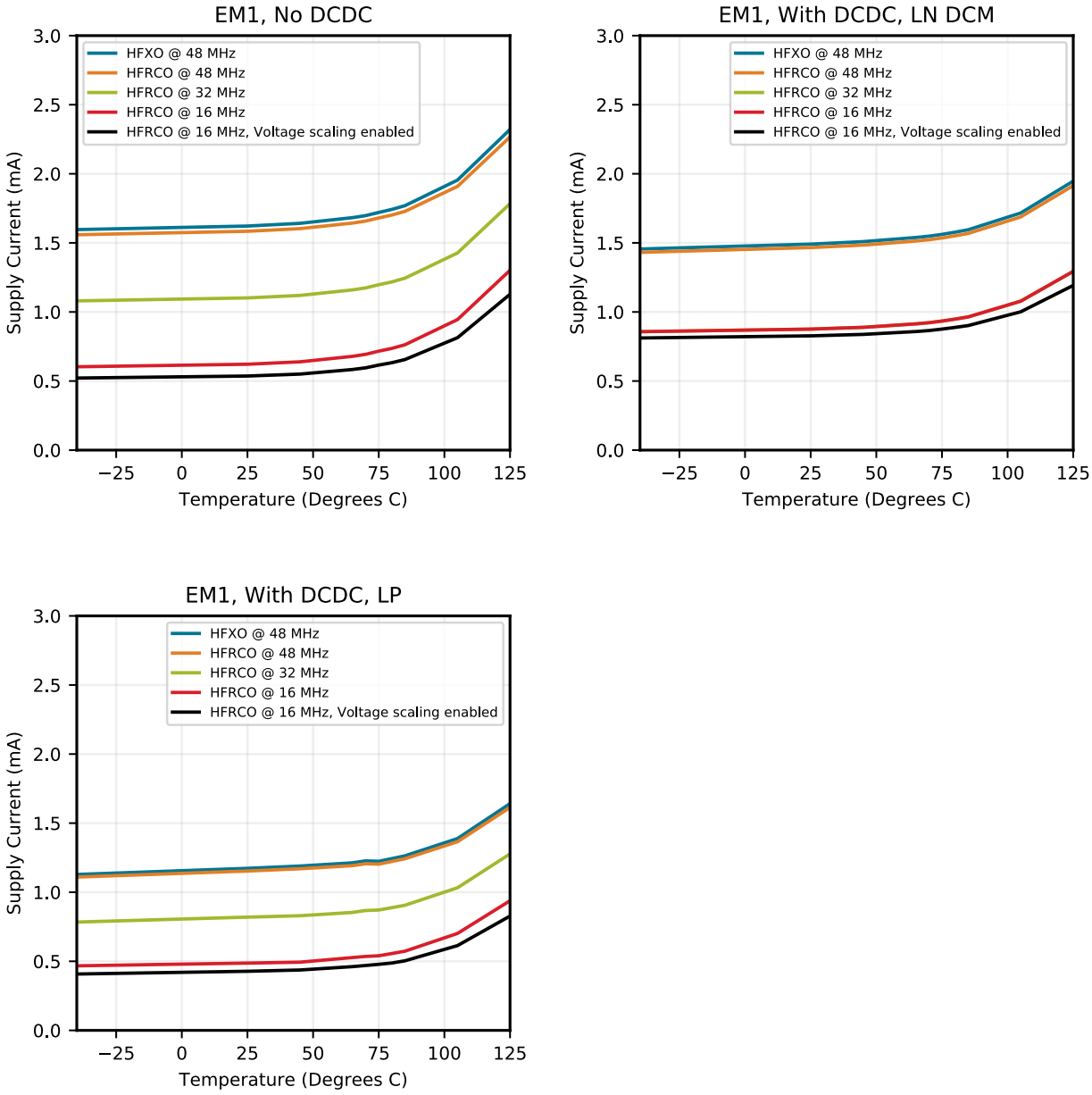

Figure 4.4. EM1 Sleep Mode Typical Supply Current vs. Temperature

Typical supply current for EM2, EM3 and EM4H using standard software libraries from Silicon Laboratories.

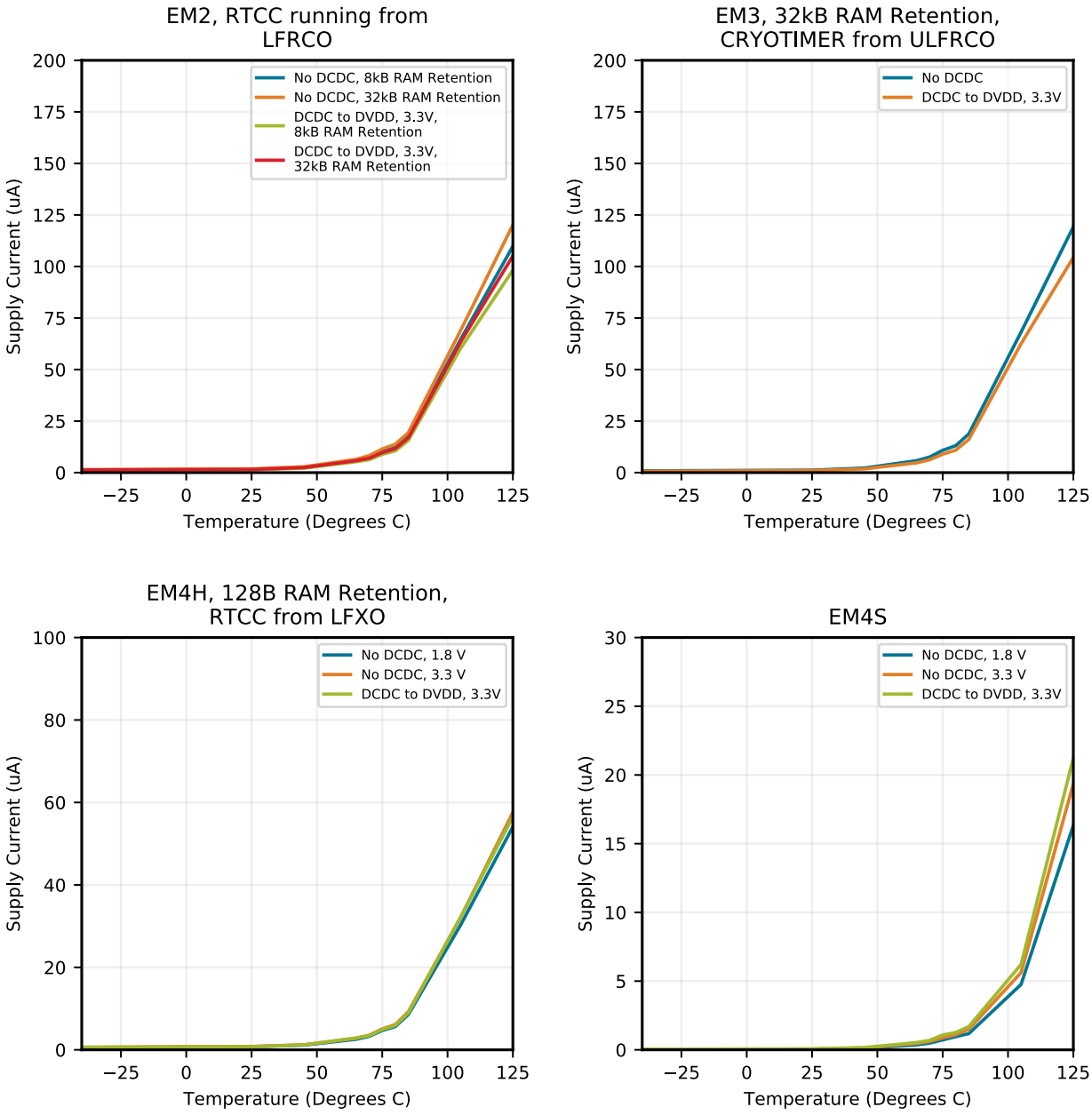

Figure 4.5. EM2, EM3, EM4H and EM4S Typical Supply Current vs. Temperature

5.7 EFM32TG11B3xx in QFN64 Device Pinout

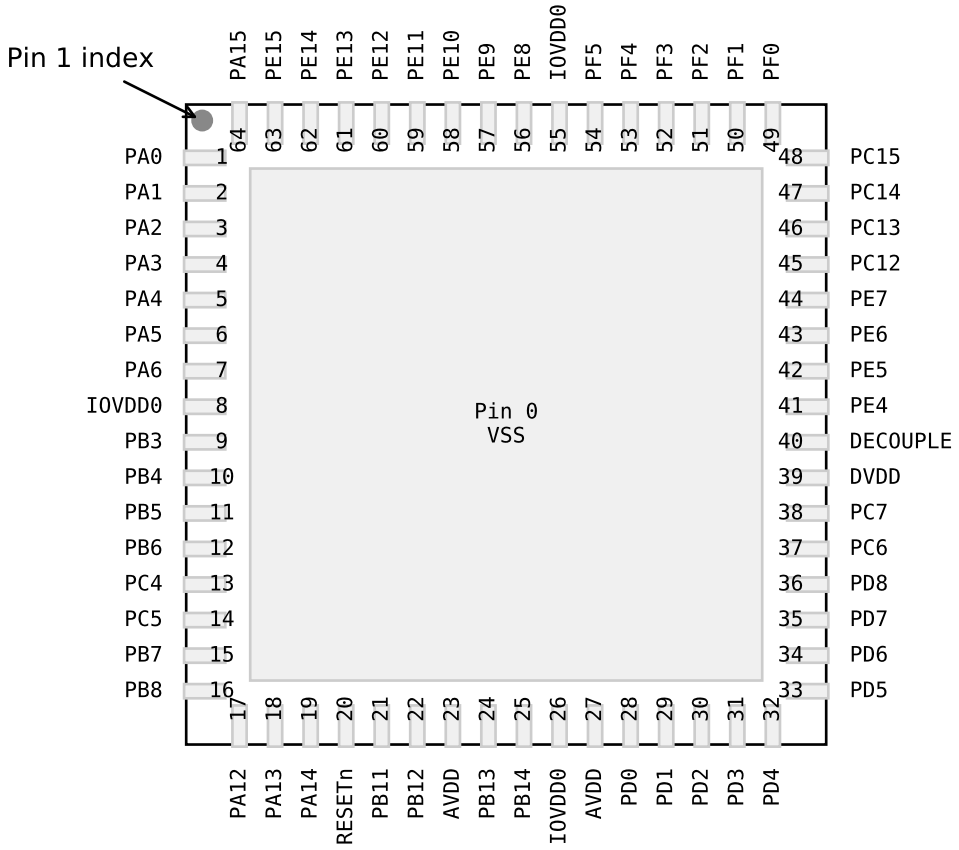

Figure 5.7. EFM32TG11B3xx in QFN64 Device Pinout

The following table provides package pin connections and general descriptions of pin functionality. For detailed information on the supported features for each GPIO pin, see 5.14 GPIO Functionality Table or 5.15 Alternate Functionality Overview.

Table 5.7. EFM32TG11B3xx in QFN64 Device Pinout

Pin Name	Pin(s)	Description	Pin Name	Pin(s)	Description
VREGVSS	0	Voltage regulator VSS	PA0	1	GPIO
PA1	2	GPIO	PA2	3	GPIO
PA3	4	GPIO	PA4	5	GPIO
PA5	6	GPIO	PA6	7	GPIO
IOVDD0	8 26 55	Digital IO power supply 0.	PB3	9	GPIO
PB4	10	GPIO	PB5	11	GPIO

5.8 EFM32TG11B1xx in QFN64 Device Pinout

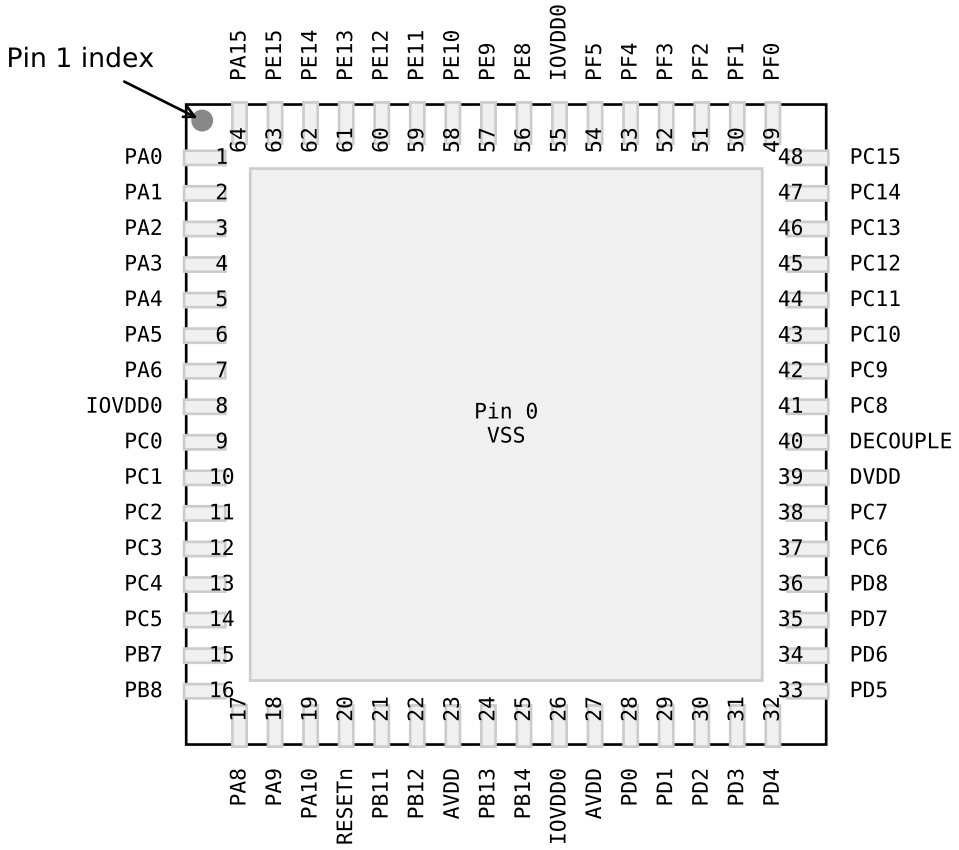

Figure 5.8. EFM32TG11B1xx in QFN64 Device Pinout

The following table provides package pin connections and general descriptions of pin functionality. For detailed information on the supported features for each GPIO pin, see 5.14 GPIO Functionality Table or 5.15 Alternate Functionality Overview.

Table 5.8. EFM32TG11B1xx in QFN64 Device Pinout

Pin Name	Pin(s)	Description	Pin Name	Pin(s)	Description
VREGVSS	0	Voltage regulator VSS	PA0	1	GPIO
PA1	2	GPIO	PA2	3	GPIO
PA3	4	GPIO	PA4	5	GPIO
PA5	6	GPIO	PA6	7	GPIO
IOVDD0	8 26 55	Digital IO power supply 0.	PC0	9	GPIO (5V)
PC1	10	GPIO (5V)	PC2	11	GPIO (5V)

Alternate	LOCATION		
Functionality	0 - 3	4 - 7	Description
LCD_SEG9	0: PE13		LCD segment line 9.
LCD_SEG10	0: PE14		LCD segment line 10.
LCD_SEG11	0: PE15		LCD segment line 11.
LCD_SEG12	0: PA15		LCD segment line 12.
LCD_SEG13	0: PA0		LCD segment line 13.
LCD_SEG14	0: PA1		LCD segment line 14.
LCD_SEG15	0: PA2		LCD segment line 15.
LCD_SEG16	0: PA3		LCD segment line 16.
LCD_SEG17	0: PA4		LCD segment line 17.
LCD_SEG18	0: PA5		LCD segment line 18.
LCD_SEG19	0: PA6		LCD segment line 19.
LCD_SEG20 / LCD_COM4	0: PB3		LCD segment line 20. This pin may also be used as LCD COM line 4
LCD_SEG21 / LCD_COM5	0: PB4		LCD segment line 21. This pin may also be used as LCD COM line 5

Table 6.2. TQFP80 PCB Land Pattern Dimensions

Dimension	Min	Max
C1	13.30	13.40
C2	13.30	13.40
E	0.50 BSC	
X	0.20	0.30
Y	1.40	1.50

Note:

1. All dimensions shown are in millimeters (mm) unless otherwise noted.
2. This Land Pattern Design is based on the IPC-7351 guidelines.
3. All metal pads are to be non-solder mask defined (NSMD). Clearance between the solder mask and the metal pad is to be 60 µm minimum, all the way around the pad.
4. A stainless steel, laser-cut and electro-polished stencil with trapezoidal walls should be used to assure good solder paste release.
5. The stencil thickness should be 0.125 mm (5 mils).
6. The ratio of stencil aperture to land pad size can be 1:1 for all pads.
7. A No-Clean, Type-3 solder paste is recommended.
8. The recommended card reflow profile is per the JEDEC/IPC J-STD-020 specification for Small Body Components.

6.3 TQFP80 Package Marking

Figure 6.3. TQFP80 Package Marking

The package marking consists of:

- PPPPPPPPPP – The part number designation.
- TTTTTT – A trace or manufacturing code. The first letter is the device revision.
- YY – The last 2 digits of the assembly year.
- WW – The 2-digit workweek when the device was assembled.

Table 9.1. QFN64 Package Dimensions

Dimension	Min	Typ	Max
A	0.70	0.75	0.80
A1	0.00	—	0.05
b	0.20	0.25	0.30
A3	0.203 REF		
D	9.00 BSC		
e	0.50 BSC		
E	9.00 BSC		
D2	7.10	7.20	7.30
E2	7.10	7.20	7.30
L	0.40	0.45	0.50
L1	0.00	—	0.10
aaa	0.10		
bbb	0.10		
ccc	0.10		
ddd	0.05		
eee	0.08		

Note:
1. All dimensions shown are in millimeters (mm) unless otherwise noted.
2. Dimensioning and Tolerancing per ANSI Y14.5M-1994.
3. Recommended card reflow profile is per the JEDEC/IPC J-STD-020 specification for Small Body Components.

11. QFN32 Package Specifications

11.1 QFN32 Package Dimensions

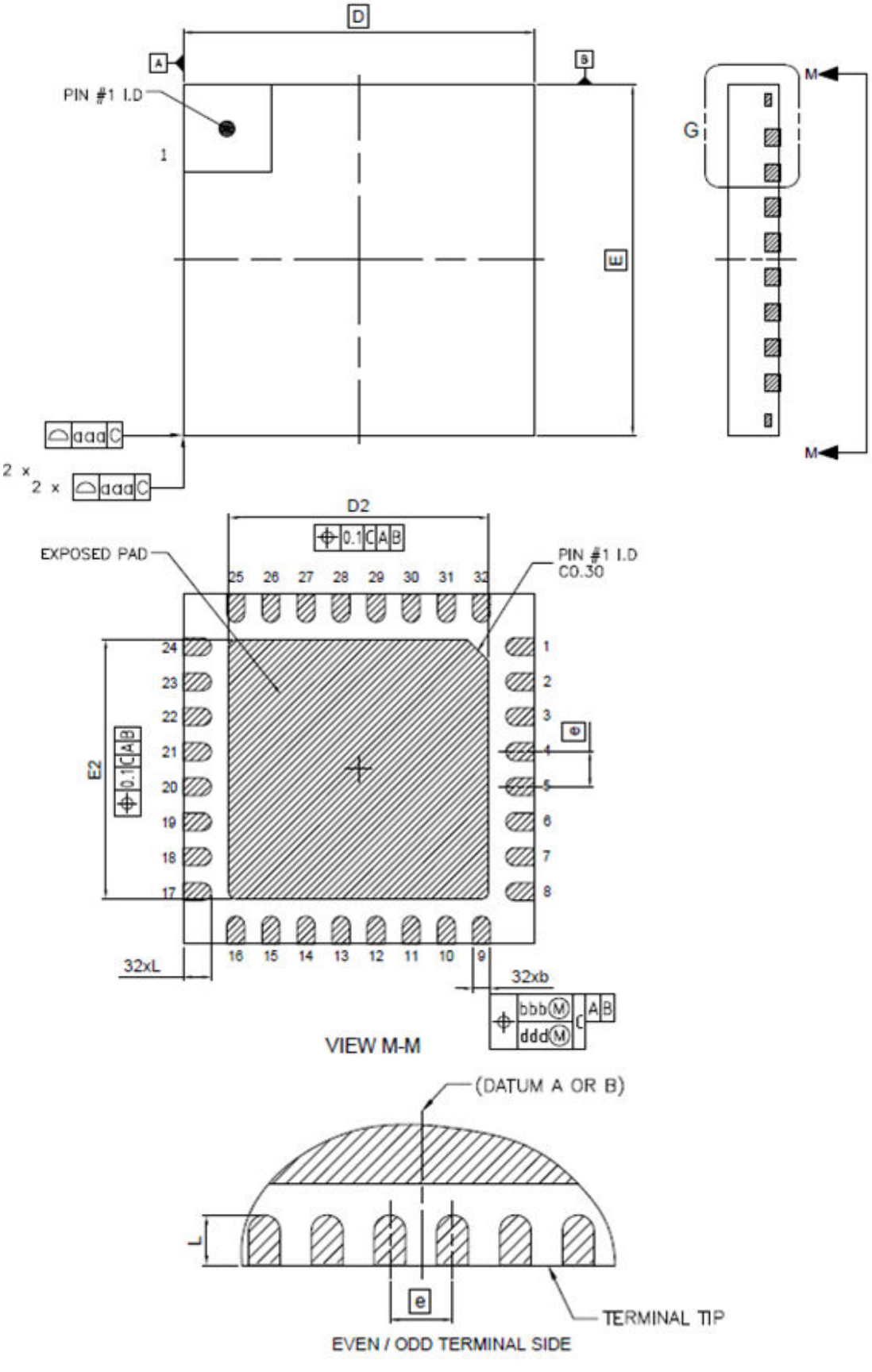

Table 11.2. QFN32 PCB Land Pattern Dimensions

Dimension	Typ
C1	5.00
C2	5.00
E	0.50
X1	0.30
Y1	0.80
X2	3.80
Y2	3.80

Note:

1. All dimensions shown are in millimeters (mm) unless otherwise noted.
2. This Land Pattern Design is based on the IPC-7351 guidelines.
3. All metal pads are to be non-solder mask defined (NSMD). Clearance between the solder mask and the metal pad is to be 60 µm minimum, all the way around the pad.
4. A stainless steel, laser-cut and electro-polished stencil with trapezoidal walls should be used to assure good solder paste release.
5. The stencil thickness should be 0.125 mm (5 mils).
6. The ratio of stencil aperture to land pad size can be 1:1 for all perimeter pads.
7. A 2x2 array of 0.9 mm square openings on a 1.2 mm pitch should be used for the center ground pad.
8. A No-Clean, Type-3 solder paste is recommended.
9. The recommended card reflow profile is per the JEDEC/IPC J-STD-020 specification for Small Body Components.